SILICON NPN TRANSISTOR
EPITAXIAL PLANAR TYPE (PCT PROCESS)

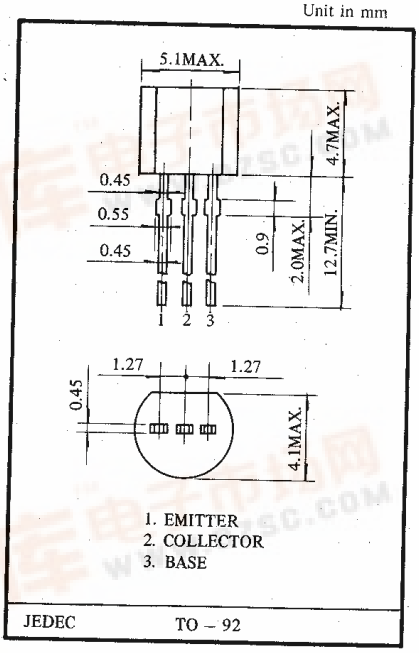
2SC3202

APPLICATIONS

- Low Frequency, Low Power Amplifiers
- General-driver Stage Amplifiers
- General purpose Switching Applications

- Excellent h_{FE} vs. Collector Current Characteristics, $h_{FE}(2)$ =25min. at V_{CE}=6V, I_C=400mA
- Ic max.=500mA
- Pc max.=500mW
- Complementary to the 2SA 1270

Unit in mm



1. EMITTER
2. COLLECTOR
3. BASE

JEDEC TO－92

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector－Base Voltage	V_{CBO}	35	V
Collector－Emitter Voltage	V_{CEO}	30	V
Emitter－Base Voltage	V_{EBO}	5	V
Collector Current	I_C	500	mA

CHARACTERISTIC	SYMBOL	RATING	UNIT
Emitter Current	I_E	−500	mA
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	−55～150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut off Current	I_{CBO}	V_{CB}=35V, I_E=0	−	−	0.1	μA
Emitter Cut off Current	I_{EBO}	V_{EB}=5V, I_C=0	−	−	0.1	μA
DC Current Gain (1)	$h_{FE}(1)$	V_{CE}=1V, I_C=100mA	70	−	240	
DC Current Gain (2)	$h_{FE}(2)$ (Pulsed)	V_{CE}=6V, I_C=400mA	25	−	−	
Collector－Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=100mA, I_B=10mA	−	0.1	0.25	V
Base－Emitter Voltage	V_{BE}	I_C=100mA, V_{CE}=1V	−	0.8	0.1	V
Transition Frequency	f_T	V_{CE}=6V, I_E=−20mA	−	300	−	MHz
Output Capacitance	C_{ob}	V_{CB}=6V, I_E=0, f=1MHz	−	7	−	pF

NOTE: According to h_{FE} (1), Classified as follows.

O	70－140	Y	120～240